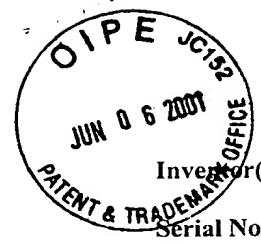


IN THE
UNITED STATES PATENT AND TRADEMARK OFFICE



Inventor(s): Jong-Ho LEE, et al.

Serial No.: 09/776,059 Examiner: Not Yet Assigned

Filing Date: February 1, 2001 Group Art Unit: 1773

Title: DIELECTRIC LAYER FOR SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

Box DD
ASSISTANT COMMISSIONER FOR PATENTS
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is submitted:

under 37 CFR 1.97 (b), or
 (Within three months of filing national application; or date of entry of International application; or before mailing date of first office action on the merits; whichever occurs last)

under 37 CFR 1.97 (c) together with either a:
 Statement under 37 CFR 1.97 (e), or
 a \$240 fee under 37 CFR 1.17 (p), or
 (After mailing of first Office Action, but prior to Notice of Allowance or Final Office Action)

under 37 CFR 1.97 (d) together with either:
 Statement under 37 CFR 1.97 (e),
 Applicant hereby petitions for the consideration of the accompanying information disclosure statement (37 C.F.R. §1.97(d)(ii)).
 a \$130.00 petition fee set forth in 37 CFR 1.17 (i)(1).
 (Filed after final action or notice of allowance, whichever occurs first, but before payment of the issue fee)

Applicant(s) submit herewith Form PTO 1449- Information Disclosure Citation together with copies of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe(s) may be material to the examination of this application and for which there may be a duty to disclose in accordance with 37 CFR 1.56.

It is requested that the information disclosed herein be made of record in this application.

Any deficiency or overpayment should be charged or credited to deposit account number 13-1703. A duplicate copy of this sheet is enclosed.



20575

PATENT TRADEMARK OFFICE

Respectfully submitted,

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**PATENT APPLICATION**

Docket No.: 4591-170
Applicant: Jong-ho LEE, et al.
Filing Date: February 1, 2001

Serial No. 09/776,059
Group: 1773

**INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)****U.S. PATENT DOCUMENTS**

<u>Exam Init</u>	<u>Ref</u>	<u>Document Number</u>	<u>Issue Date</u>	<u>Name</u>	<u>Class</u>	<u>Sub- Class</u>
_____	_____	5,923,056	07/13/99	Lee, et al.		
_____	_____	6,013,553	01/11/00	Wallace, et al.		
_____	_____	6,020,024	02/01/00	Maiti, et al.		
_____	_____	6,020,243	02/01/00	Wallace, et al.		
_____	_____	6,060,755	05/09/00	Ma, et al.		

FOREIGN PATENT DOCUMENTS

	<u>Document Number</u>	<u>Publication Date</u>	<u>Country</u>	<u>Name</u>
_____	_____			
_____	_____			
_____	_____			

OTHER DOCUMENTS

Exam
Init Ref (Including Author, Title, Date, Pertinent Pages, etc.)

_____ _____ Wilk, G.D. and Wallace, R.M.; "Electrical Properties of hafnium silicate gate dielectrics deposited directly on silicon"; Applied Physics Letters; pp 2854-2856 (1999)

Examiner: _____

Date Considered: _____